



30V N-Channel NexFET™ Power MOSFETs

Check for Samples: CSD17304Q3

FEATURES

- · Optimized for 5V Gate Drive
- Ultralow Q_g and Q_{gd}
- Low Thermal Resistance
- Avalanche Rated
- Pb Free Terminal Plating
- RoHS Compliant
- Halogen Free
- SON 3.3-mm × 3.3-mm Plastic Package

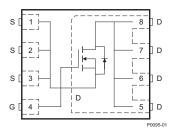
APPLICATIONS

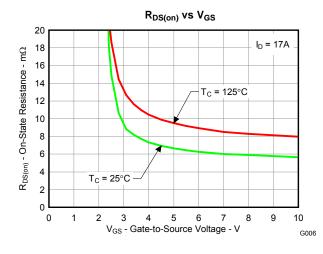
- Notebook Point of Load
- Point-of-Load Synchronous Buck in Networking, Telecom, and Computing Systems

DESCRIPTION

The NexFET™ power MOSFET has been designed to minimize losses in power conversion applications and optimized for 5V gate drive applications.







PRODUCT SUMMARY

V_{DS}	Drain to Source Voltage	30			
Q_g	Gate Charge Total (4.5V)	5.1	nC		
Q_{gd}	Gate Charge Gate to Drain	1.1	nC		
		$V_{GS} = 3V$	9.8	mΩ	
R _{DS(on)}	Drain to Source On Resistance	$V_{GS} = 4.5V$ 6.9		mΩ	
		V _{GS} = 8V 5.9		mΩ	
V _{GS(th)}	Threshold Voltage	1.3		V	

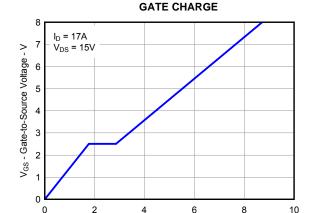
ORDERING INFORMATION

Device	Package	Media Qty		Ship
CSD17304Q3	SON 3.3-mm × 3.3-mm Plastic Package	13-Inch Reel	2500	Tape and Reel

ABSOLUTE MAXIMUM RATINGS

T _A = 2	5°C unless otherwise stated	VALUE	UNIT
V_{DS}	Drain to Source Voltage	30	٧
V_{GS}	Gate to Source Voltage	+10 / -8	٧
	Continuous Drain Current, T _C = 25°C	56	Α
I _D	Continuous Drain Current ⁽¹⁾	15	Α
I _{DM}	Pulsed Drain Current, T _A = 25°C ⁽²⁾	88	Α
P_D	Power Dissipation ⁽¹⁾	2.7	W
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C
E _{AS}	Avalanche Energy, Single Pulse I _D = 42A, L = 0.1mH, R _G = 25Ω	88	mJ

- (1) Typical $R_{\theta JA}=46^{\circ}\text{C/W}$ on a 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu pad on a 0.06-inch (1.52-mm) thick FR4 PCB.
- (2) Pulse duration ≤300μs, duty cycle ≤2%



Q_q - Gate Charge - nC

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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ELECTRICAL CHARACTERISTICS

 $(T_A = 25^{\circ}C)$ unless otherwise stated)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static Cl	haracteristics	•	•			
BV _{DSS}	Drain to Source Voltage	V _{GS} = 0V, I _D = 250μA	30			V
I _{DSS}	Drain to Source Leakage Current	V _{GS} = 0V, V _{DS} = 24V			1	μА
I _{GSS}	Gate to Source Leakage Current	$V_{DS} = 0V, V_{GS} = +10 / -8V$			100	nA
$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, \ I_D = 250 \mu A$	0.9	1.3	1.8	V
		$V_{GS} = 3V, I_{D} = 17A$		9.8	12.6	$m\Omega$
R _{DS(on)}	Drain to Source On Resistance	$V_{GS} = 4.5V, I_D = 17A$		6.9	8.8	mΩ
		$V_{GS} = 8V, I_{D} = 17A$		5.9	7.5	mΩ
9 _{fs}	Transconductance	V _{DS} = 15V, I _D = 17A		48		S
Dynamic	Characteristics		·			
C _{ISS}	Input Capacitance			735	955	рF
Coss	Output Capacitance	$V_{GS} = 0V, V_{DS} = 15V,$ f = 1MHz		390	505	рF
C _{RSS}	Reverse Transfer Capacitance	1 - 11/11/2		29	38	pF
R _g	Series Gate Resistance			1.1	2.2	Ω
Qg	Gate Charge Total (4.5V)			5.1	6.6	nC
Q_{gd}	Gate Charge Gate to Drain	\/ 45\/ 47\		1.1		nC
Q _{gs}	Gate Charge Gate to Source	V _{DS} = 15V, I _D = 17A		1.8		nC
Qg(th)	Gate Charge at Vth			0.9		nC
Q _{OSS}	Output Charge	V _{DS} = 13V, V _{GS} = 0V	9.9			nC
t _{d(on)}	Turn On Delay Time			5.1		ns
t _r	Rise Time	$V_{DS} = 15V, V_{GS} = 4.5V,$		9.1		ns
t _{d(off)}	Turn Off Delay Time	$I_D = 17A$, $R_G = 2\Omega$		10.4		ns
t _f	Fall Time			3.1		ns
Diode Cl	haracteristics					
V _{SD}	Diode Forward Voltage	I _{DS} = 17A, V _{GS} = 0V		0.85	1	V
Q _{rr}	Reverse Recovery Charge	V _{DD} = 13V, I _F = 17A,		14.5		nC
t _{rr}	Reverse Recovery Time	di/dt = 300A/μs		17.3		ns

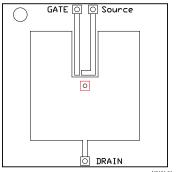
THERMAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

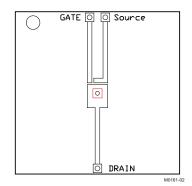
	PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Thermal Resistance Junction to Case ⁽¹⁾			3.9	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient ⁽¹⁾⁽²⁾			57	°C/W

 $R_{\theta JC}$ is determined with the device mounted on a 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu pad on a 1.5-inch × 1.5-inch (3.81-cm × 3.81-cm), 0.06-inch (1.52-mm) thick FR4 PCB. $R_{\theta JC}$ is specified by design, whereas $R_{\theta JA}$ is determined by the user's board design. Device mounted on FR4 material with 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu.





Max $R_{\theta JA} = 57^{\circ}C/W$ when mounted on 1 inch² (6.45 cm²) of 2-oz. (0.071-mm thick) Cu.



Max $R_{\theta JA} = 158^{\circ}C/W$ when mounted on a minimum pad area of 2-oz. (0.071-mm thick) Cu.

TYPICAL MOSFET CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

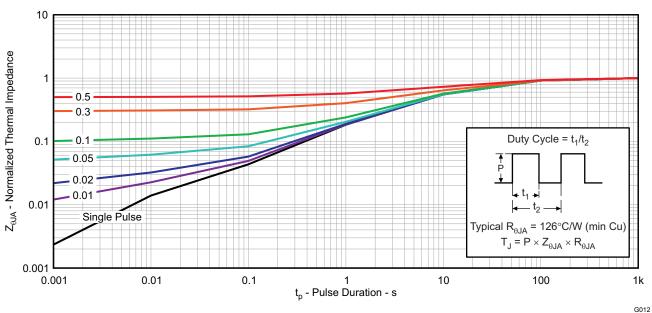


Figure 1. Transient Thermal Impedance

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Product Folder Link(s): CSD17304Q3



TYPICAL MOSFET CHARACTERISTICS (continued)

(T_A = 25°C unless otherwise stated)

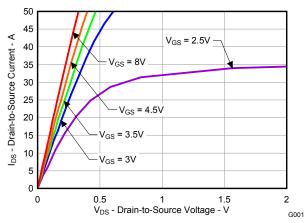


Figure 2. Saturation Characteristics

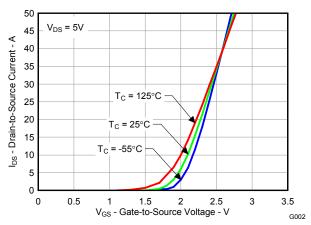


Figure 3. Transfer Characteristics

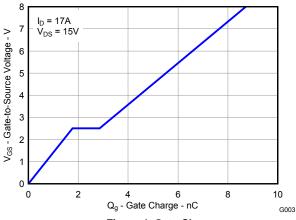


Figure 4. Gate Charge

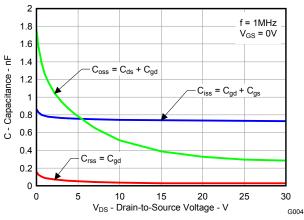


Figure 5. Capacitance

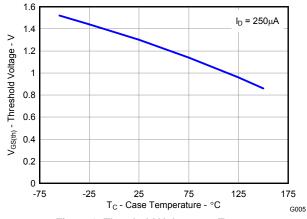


Figure 6. Threshold Voltage vs. Temperature

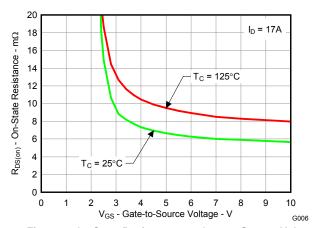


Figure 7. On-State Resistance vs. Gate-to-Source Voltage



TYPICAL MOSFET CHARACTERISTICS (continued)

(T_A = 25°C unless otherwise stated)

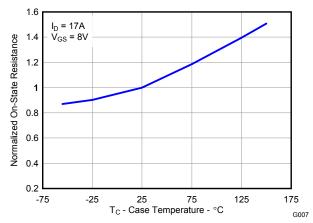


Figure 8. Normalized On-State Resistance vs. Temperature

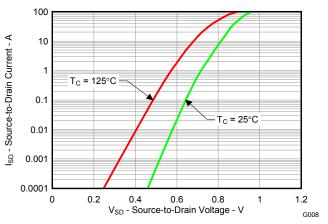


Figure 9. Typical Diode Forward Voltage

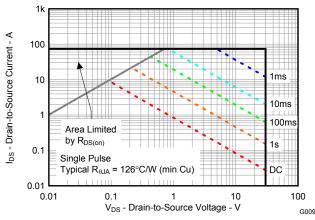


Figure 10. Maximum Safe Operating Area

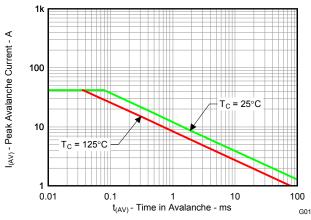


Figure 11. Single Pulse Unclamped Inductive Switching

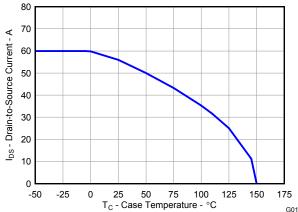
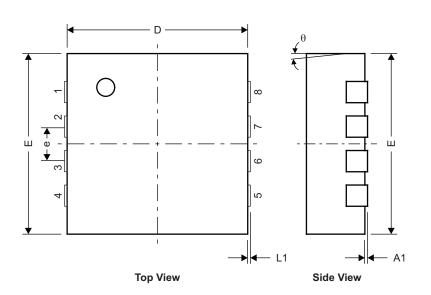


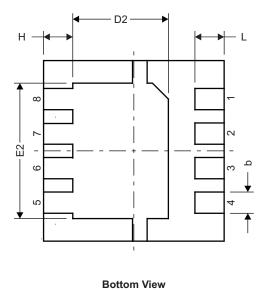
Figure 12. Maximum Drain Current vs. Temperature

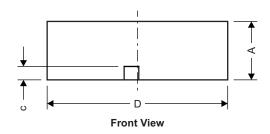


MECHANICAL DATA

Q3 Package Dimensions





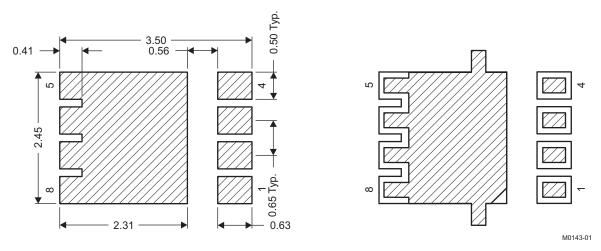


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DIM		MILLIMETERS	}	INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.950	1.000	1.100	0.037	0.039	0.043	
A1	0.000	0.000	0.050	0.000	0.000	0.002	
b	0.280	0.340	0.400	0.011	0.013	0.016	
С	0.150	0.200	0.250	0.006	0.008	0.010	
D	3.200	3.300	3.400	0.126	0.130	0.134	
D1	_	_	_	_	_	_	
D2	1.650	1.750	1.800	0.065	0.069	0.071	
Е	3.200	3.300	3.400	0.126	0.130	0.134	
E1	_	-	-	_	_	_	
E2	2.350	2.450	2.550	0.093	0.096	0.100	
е		0.650 TYP			0.026		
Н	0.35	0.450	0.550	0.014	0.018	0.022	
L	0.35	0.450	0.550	0.014	0.018	0.022	
L1	_	-	-	_	_	_	
θ	-	-	_	_		_	

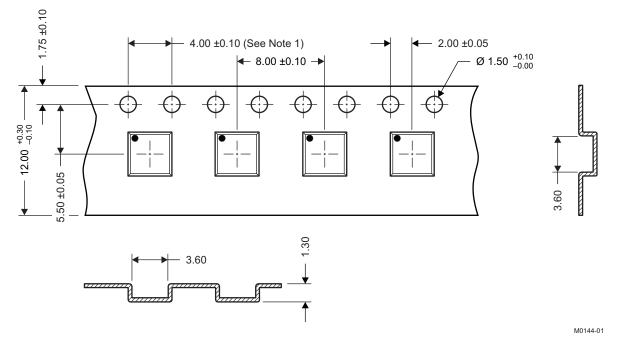


Recommended PCB Pattern



For recommended circuit layout for PCB designs, see application note SLPA005 – Reducing Ringing Through PCB Layout Techniques.

Q3 Tape and Reel Information



Notes:

- 1. 10-sprocket hole-pitch cumulative tolerance ±0.2
- 2. Camber not to exceed 1mm in 100mm, noncumulative over 250mm
- 3. Material: black static-dissipative polystyrene
- 4. All dimensions are in mm (unless otherwise specified)
- 5. Thickness: 0.30 ±0.05mm
- 6. MSL1 260°C (IR and convection) PbF reflow compatible

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REVISION HISTORY

Changes from Original (February 2010) to Revision A				
•	Deleted the Package Marking Information section			

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PACKAGING INFORMATION

Orderable part number	Status	Material type	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
CSD17304Q3	Active	Production	VSON-CLIP (DQG) 8	2500 LARGE T&R	ROHS Exempt	SN	Level-1-260C-UNLIM	-55 to 150	CSD17304
CSD17304Q3.B	Active	Production	VSON-CLIP (DQG) 8	2500 LARGE T&R	ROHS Exempt	SN	Level-1-260C-UNLIM	-55 to 150	CSD17304

⁽¹⁾ Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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⁽³⁾ RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

⁽⁴⁾ Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

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